

## AMENDMENTS TO THE SPECIFICATION

[0028] **Figure 9** shows the structure of **Figure 8** following the separation of a portion of semiconductor material 200 from the portion that includes semiconductor material 200 within via 190 and a portion of trench pad 185 including, but not limited to, the entire portion. Referring to **Figure 9**, structure 100 includes semiconductor material 200 defined as semiconductor portion 200A and semiconductor portion 200B. Semiconductor portion 200B is separated at reference numeral 218 from semiconductor portion 200A which includes semiconductor material in via 190. Photolithographic/etch techniques may be used to separate semiconductor portion 200A and semiconductor portion 200B. In this manner, semiconductor portion 200B may be used as a channel for device formation and semiconductor portion 200A isolated. One reason to separate a portion of the semiconductor material that includes the portion extending through the via is that that portion containing epitaxial layer 130 is electrically disconnected from semiconductor portion 200B. Thus, where the first dielectric layer ~~160~~140 is a dielectric material such as SiO<sub>2</sub>, that portion of structure 100 including semiconductor portion 200B is a semiconductor on insulated (SOI) structure, with semiconductor portion 200B serving as a device channel. Semiconductor portion 200B has a length, L<sub>0</sub>, that, in one embodiment, is less than L<sub>1</sub>.